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PATENT ABSTRACTS OF JAPAN

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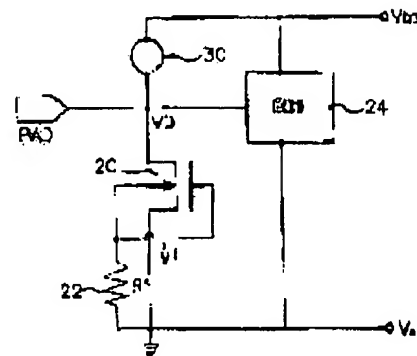
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(54) ELECTROSTATIC PROTECTIVE DEVICE

(57)Abstract:

PROBLEM TO BE SOLVED: To obtain an electrostatic protective device which prevents a current concentration phenomenon and whose electrostatic protective performance is enhanced by a method wherein the gate of a MOS element is grounded through an internal resistor.

SOLUTION: An electrostatic protective device 30 is connected across the input end and the output end of an internal circuit 24 which is situated between a first power-supply voltage source VDD and a second power-supply voltage source VSS. The electrostatic protective device 30 is provided with a drain which is formed on a well region, which is connected to the input end and the output end of the internal circuit 24 and to which the first power-supply voltage source VDD is applied, with a source which is connected in common across the second power-supply voltage source VSS and the well region and with a MOS element 20 which is connected to a well contact part and which has a gate. In addition, the electrostatic protective device is provided with an internal resistor 22 connected to the gate of the MOS element 20 through the well contact part. For example, a MOS element 20 is an N-channel conductivity-type MOS transistor. In addition, an internal resistance 22 is formed as a well resistance, and its resistance value is set at several Ω to several hundred Ω .



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